# Richard J Potter

List of Publications by Year
in descending order

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| 67 | 1,630 | 236833 25 | 315616 38 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 68 | 68 | 68 | 2347 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Oxygen deficient Î±-Fe<sub>2</sub>O<sub>3</sub> photoelectrodes: a balance between enhanced electrical properties and trap-mediated losses. Chemical Science, 2015, 6, 4009-4016. | 3.7 | 92 |
| 2 | Some recent developments in the MOCVD and ALD of high-Îº dielectric oxides. Journal of Materials Chemistry, 2004, 14, 3101-3112. | 6.7 | 78 |
| 3 | Silicon nanoparticles generated by femtosecond laser ablation in a liquid environment. Journal of Nanoparticle Research, 2010, 12, 573-580. | 0.8 | 71 |
| 4 | Permittivity enhancement of hafnium dioxide high-Îº films by cerium doping. Applied Physics Letters, 2008, 93, . | 1.5 | 67 |
| 5 | Core Levels, Band Alignments, and Valence-Band States in CuSbS<sub>2</sub> for Solar Cell Applications. ACS Applied Materials & Interfaces, 2017, 9, 41916-41926. | 4.0 | 67 |
| 6 | Deposition of HfO2, Gd2O3 and PrOx by Liquid Injection ALD Techniques. Chemical Vapor Deposition, 2005, 11, 159-169. | 1.4 | 61 |
| 7 | Modification of the electrical properties of PEDOT:PSS by the incorporation of ZnO nanoparticles synthesized by laser ablation. Chemical Physics Letters, 2010, 484, 283-289. | 1.2 | 58 |
| 8 | Optical properties of GaNAs and GaInAsN quantum wells. Journal of Physics Condensed Matter, 2004, 16, S3387-S3412. | 0.7 | 56 |
| 9 | Recent developments in the MOCVD and ALD of rare earth oxides and silicates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 97-104. | 1.7 | 56 |
| 10 | The role of nitrogen doping in ALD Ta2O5 and its influence on multilevel cell switching in RRAM. Applied Physics Letters, 2017, 110, . | 1.5 | 54 |
| 11 | IIâ€“VI semiconductor nanoparticles synthesized by laser ablation. Applied Physics A: Materials Science and Processing, 2009, 94, 641-647. | 1.1 | 50 |
| 12 | Atomic layer deposition of TaN and Ta3N5 using pentakis(dimethylamino)tantalum and either ammonia or monomethylhydrazine. Journal of Crystal Growth, 2011, 331, 33-39. | 0.7 | 43 |
| 13 | The Effects of Zr Doping on the Optical, Electrical and Microstructural Properties of Thin ZnO Films Deposited by Atomic Layer Deposition. Materials, 2015, 8, 7230-7240. | 1.3 | 43 |
| 14 | Biotransformation of Silver Released from Nanoparticle Coated Titanium Implants Revealed in Regenerating Bone. ACS Applied Materials & Interfaces, 2017, 9, 21169-21180. | 4.0 | 39 |
| 15 | Interaction Strength between the Highly Localised Nitrogen States and the Extended Semiconductor Matrix States in GaInNAs. Physica Status Solidi A, 2001, 187, 623-632. | 1.7 | 37 |
| 16 | Picosecond laser patterning of PEDOT:PSS thin films. Synthetic Metals, 2011, 161, 431-439. | 2.1 | 37 |
| 17 | Band Alignments, Band Gap, Core Levels, and Valence Band States in Cu<sub>3</sub>BiS<sub>3</sub> for Photovoltaics. ACS Applied Materials & Interfaces, 2019, 11, 27033-27047. | 4.0 | 37 |
| 18 | Atomic Layer Deposition of a Silver Nanolayer on Advanced Titanium Orthopedic Implants Inhibits Bacterial Colonization and Supports Vascularized de Novo Bone Ingrowth. Advanced Healthcare Materials, 2017, 6, 1700033. | 3.9 | 35 |

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|---|---|---|---|
| 19 | S-shaped behaviour of the temperature-dependent energy band gap in dilute nitrides. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 242-244. | 1.3 | 34 |
| 20 | Deposition of HfO2 and ZrO2 films by liquid injection MOCVD using new monomeric alkoxide precursors. Journal of Materials Chemistry, 2005, 15, 1896. | 6.7 | 33 |
| 21 | Spectroellipsometric assessment of HfO2 thin films. Thin Solid Films, 2006, 515, 623-626. | 0.8 | 28 |
| 22 | CdSe nanoparticles synthesized by laser ablation. Europhysics Letters, 2008, 84, 47001. | 0.7 | 27 |
| 23 | High-k materials and their response to gamma ray radiation. Journal of Vacuum Science & Technology B, 2009, 27, 411. | 1.3 | 27 |
| 24 | CdTe nanoparticles synthesized by laser ablation. Applied Physics Letters, 2009, 95, . | 1.5 | 26 |
| 25 | Directing the mechanism of CO<sub>2</sub> reduction by a Mn catalyst through surface immobilization. Physical Chemistry Chemical Physics, 2018, 20, 6811-6816. | 1.3 | 26 |
| 26 | Self-limiting atomic layer deposition of conformal nanostructured silver films. Applied Surface Science, 2016, 364, 789-797. | 3.1 | 25 |
| 27 | The effect of In/N ratio on the optical quality and lasing threshold in GaxIn1â^'xAs1â^'yNy/GaAs laser structures. Superlattices and Microstructures, 2001, 29, 169-186. | 1.4 | 23 |
| 28 | Growth of Neodymium Oxide This Films by Liquid Injection MOCVD Using a New Neodymium Alkoxide Precursor. Chemical Vapor Deposition, 2004, 10, 301-305. | 1.4 | 23 |
| 29 | Compositional variation in as-grown GaInNAs/GaAs quantum well structures. Journal of Crystal Growth, 2001, 233, 1-4. | 0.7 | 21 |
| 30 | Characterization of hafnium aluminate gate dielectrics deposited by liquid injection metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 4119-4121. | 1.5 | 21 |
| 31 | Enhanced switching stability in Ta2O5 resistive RAM by fluorine doping. Applied Physics Letters, 2017, 111, . | 1.5 | 21 |
| 32 | Deposition of Pr- and Nd-aluminate by Liquid Injection MOCVD and ALD Using Single-Source Heterometallic Alkoxide Precursors. Chemistry of Materials, 2007, 19, 4796-4803. | 3.2 | 20 |
| 33 | Investigation of optical and electronic properties of hafnium aluminate films deposited by Metalâ€“Organic Chemical Vapour Deposition. Thin Solid Films, 2007, 515, 3772-3778. | 0.8 | 19 |
| 34 | Growth of Gadolinium Oxide This Films by Liquid Injection MOCVD Using a New Gadolinium Alkoxide Precursor. Chemical Vapor Deposition, 2004, 10, 306-310. | 1.4 | 18 |
| 35 | The influence of tertiary butyl hydrazine as a co-reactant on the atomic layer deposition of silver. Applied Surface Science, 2017, 399, 123-131. | 3.1 | 18 |
| 36 | Growth of Hafnium Aluminate Thin Films by Liquid Injection MOCVD Using Alkoxide Precursors. Chemical Vapor Deposition, 2004, 10, 275-279. | 1.4 | 16 |

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|---|---|---|---|
| 37 | Vacuum ultraviolet photochemical selective area atomic layer deposition of Al2O3 dielectrics. AIP Advances, 2015, 5, . | 0.6 | 16 |
| 38 | Gadolinium nitride films deposited using a PEALD based process. Journal of Crystal Growth, 2012, 338, 111-117. | 0.7 | 15 |
| 39 | Tuning the electrical properties of ZnO thin-film transistors by thermal annealing in different gases. Thin Solid Films, 2014, 552, 192-195. | 0.8 | 15 |
| 40 | Stable Ta<sub>2</sub>O<sub>5</sub> Overlayers on Hematite for Enhanced Photoelectrochemical Water Splitting Efficiencies. ChemPhotoChem, 2018, 2, 183-189. | 1.5 | 15 |
| 41 | In-plane photovoltage and photoluminescence studies in sequentially grown GaInNAs and GaInAs quantum wells. Journal of Applied Physics, 2003, 93, 2440-2448. | 1.1 | 14 |
| 42 | Deposition of HfO2 Films by Liquid Injection MOCVD Using a New Monomeric Alkoxide Precursor, [Hf(dmop)4]. Chemical Vapor Deposition, 2005, 11, 299-305. | 1.4 | 14 |
| 43 | Polymer-nanoparticle composites composed of PEDOT:PSS and nanoparticles of Ag synthesised by laser ablation. Colloid and Polymer Science, 2012, 290, 213-220. | 1.0 | 13 |
| 44 | Effect of nitrogen fraction on the temperature dependence of GaNAs/GaAs quantum-well emission. Applied Physics Letters, 2003, 82, 3400-3402. | 1.5 | 12 |
| 45 | Synthesis and characterisation of four new heterometal alkoxides: potential precursors for the MOCVD of ferroelectric oxides. Journal of Materials Chemistry, 2004, 14, 887. | 6.7 | 12 |
| 46 | Optical and electrical characterization of hafnium oxide deposited by liquid injection atomic layer deposition. Microelectronics Reliability, 2007, 47, 825-829. | 0.9 | 10 |
| 47 | Comparison of atomic layer deposited Al2O3 and (Ta2O5)0.12(Al2O3)0.88 gate dielectrics on the characteristics of GaN-capped AlGaN/GaN metal-oxide-semiconductor high electron mobility transistors. Journal of Applied Physics, 2019, 126, . | 1.1 | 9 |
| 48 | Optical properties of GaInNAs/GaAs quantum wells. Solid-State Electronics, 2003, 47, 483-487. | 0.8 | 8 |
| 49 | Atomic vapour deposition (AVD) of SrBi2Ta2O9 using an all alkoxide precursor. Journal of Crystal Growth, 2004, 272, 778-784. | 0.7 | 8 |
| 50 | Tuneable electrical properties of hafnium aluminate gate dielectrics deposited by metal organic chemical vapour deposition. Microelectronics Reliability, 2007, 47, 722-725. | 0.9 | 8 |
| 51 | VCSEL structure hot electron light emitter. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 96-100. | 1.7 | 7 |
| 52 | Band structure and optical gain in GaInAsN quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 245-246. | 1.3 | 7 |
| 53 | Charge trapping characterization of MOCVD HfO2/p-Si interfaces at cryogenic temperatures. Microelectronics Reliability, 2007, 47, 726-728. | 0.9 | 6 |
| 54 | Comparative analysis of the effects of tantalum doping and annealing on atomic layer deposited (Ta2O5)x(Al2O3)1â^'x as potential gate dielectrics for GaN/AlxGa1â^'xN/GaN high electron mobility transistors. Journal of Applied Physics, 2016, 119, . | 1.1 | 6 |

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|---|---|---|---|
| 55 | Operation of a novel hot-electron vertical-cavity surface-emitting laser. , 1998, , . | | 5 |
| 56 | Elucidation of ALD MgZnO deposition processes using low energy ion scattering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, . | 0.9 | 5 |
| 57 | Hot electron light emission from GaInAsP/InP structures with distributed Bragg reflectors. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 607-609. | 1.3 | 3 |
| 58 | The operation of a wavelength converter basedon a field effect light emitting and absorbing heterojunction. Physica Status Solidi A, 2003, 196, 496-503. | 1.7 | 3 |
| 59 | Thermal stability of hafnium silicate dielectric films deposited by a dual source liquid injection MOCVD. Journal of Materials Science: Materials in Electronics, 2004, 15, 711-714. | 1.1 | 3 |
| 60 | (Invited) Vacuum Ultraviolet Photochemical Atomic Layer Deposition of Alumina and Titania Films. ECS Transactions, 2015, 69, 139-145. | 0.3 | 3 |
| 61 | Comparison of theoretical models for interband transitions in dilute nitrides and experimental measurement. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 240-241. | 1.3 | 2 |
| 62 | 1.5-Î¼m surface emission from GaInAsP/InP HELLISH structures. , 2001, 4283, 723. | | 1 |
| 63 | Photo-induced transient spectroscopy and in-plane photovoltage in GaInNAs/GaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 250-251. | 1.3 | 1 |
| 64 | Charge trapping and interface states in hydrogen annealed HfO2â€“Si structures. Microelectronics Reliability, 2007, 47, 714-717. | 0.9 | 1 |
| 65 | The Effects of Nitrogen Incorporation on Photogenerated Carrier Dynamics in Dilute Nitrides. , 2008, , 181-197. | | 1 |
| 66 | Optical characterization of GaInNAs. , 2001, 4283, 638. | | 0 |
| 67 | A superlattice approach to the synthesis of ferroelectric Strontium Bismuth Tantalate thin films using liquid-injection-MOCVD. Materials Research Society Symposia Proceedings, 2005, 902, 1. | 0.1 | 0 |